

# 64K (8K x 8) CMOS Electrically Erasable PROM

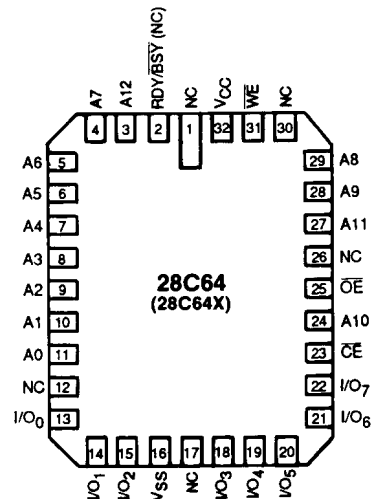
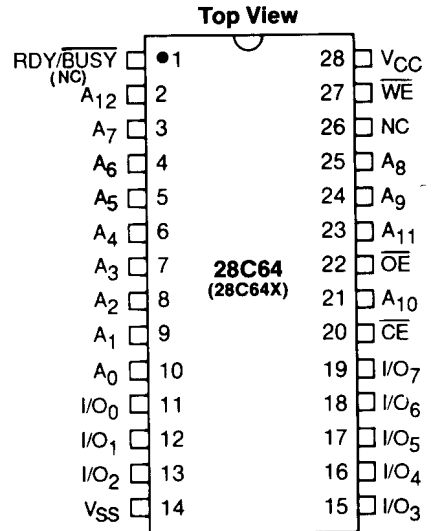
## FEATURES

- Fast Read Access Time — 150 ns
- High Performance CMOS Technology for Low Power Dissipation
  - 100  $\mu$ A Standby
  - 30 mA Active
- Fast Byte Write Time — 200  $\mu$ s or 1 ms
- High Endurance  $10^5$  Erase/Write Cycles
- Automatic Write Operation
  - Internal Control Timer
  - Auto-Clear Before Write Operation
  - On-Chip Address and Data Latches
- DATA Polling
- Ready/BUSY (Open Drain)
- Chip Clear Function
- Enhanced Data Protection
  - $V_{CC}$  Detector
  - Power-Up Timer
- Electronic Signature
  - Device Identification
  - Tracking
- Data Retention > 10 years
- 5-Volt Only Operation
- JEDEC-Approved Byte-Wide Pinout
  - 28-Pin DIP
  - 32-Pin LCC/PLCC
- Full Commercial and Industrial Temperature Ranges
  - $0^\circ$  to  $+70^\circ$  C Commercial (28C64)
  - $-40^\circ$  to  $+85^\circ$  C Industrial (28C64I)
- Also available in military temperature range
  - $-55^\circ$  to  $+125^\circ$  C Military (28C64MR)

## PIN NAMES

A <sub>0</sub> - A <sub>12</sub>	ADDRESSES
$\overline{CE}$	CHIP ENABLE
$\overline{OE}$	OUTPUT ENABLE
$\overline{WE}$	WRITE ENABLE
I/O <sub>0</sub> - I/O <sub>7</sub>	DATA INPUTS/OUTPUTS
RDY/ <u>BUSY</u>	READY/BUSY
NC	NO CONNECT

## PIN CONFIGURATION



341

Res  
006042

orig

6042

GI

**DESCRIPTION**

The General Instrument 28C64 is a low-power, high-performance 8,192 x 8 bit non-volatile Electrically Erasable and Programmable Read Only Memory with popular, easy to use features. The device is manufactured with General Instrument's advanced and reliable non-volatile CMOS technology.

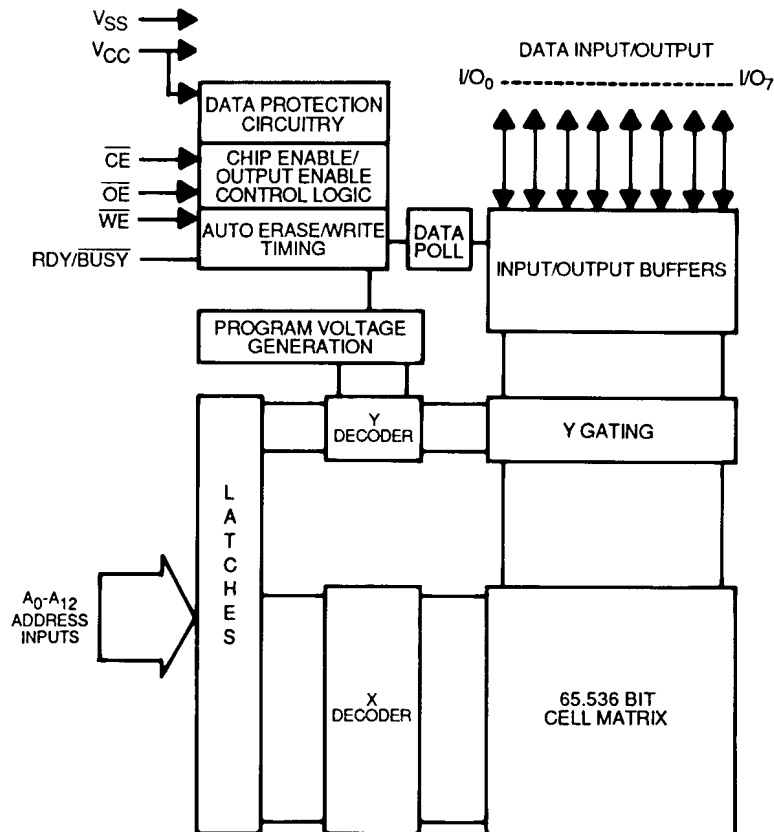
The 28C64 is accessed like a static RAM for the read or write cycles without the need of external components. During a "byte write", the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer.

To determine when the write cycle is complete, the user has a choice of monitoring the Ready/Busy out-

put or using  $\overline{\text{DATA}}$  polling. The Ready/Busy pin is an open drain output, which allows easy configuration in wired-or systems. Alternatively,  $\overline{\text{DATA}}$  polling allows the user to read the location last written to when the write operation is complete.

The 28C64 operates from a single 5V supply and is packaged in standard JEDEC-approved packages. All necessary programming voltages are internally generated and timed.

The CMOS technology offers fast access times of 150 ns (28C64-15) at low power dissipation of 30 mA. When the chip is deselected, the standby current is less than 100  $\mu\text{A}$ . The 28C64's fast memory access time allows for direct polling with microprocessors without waiting.



**FUNCTIONAL BLOCK DIAGRAM  
28C64**

**DEVICE OPERATION**

The General Instrument 28C64 has four basic modes of operation — read, standby, write inhibit, and byte write — as outlined in the following table.

MODE \ PIN	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O	Rdy/Busy <sup>(1)</sup>
READ	L	L	H	D <sub>OUT</sub>	H
STANDBY	H	X	X	High Z	H
WRITE INHIBIT	H	X	X	High Z	H
WRITE INHIBIT	X	L	X	—	H
WRITE INHIBIT	X	X	H	—	H
BYTE WRITE	L	H	L	D <sub>IN</sub>	L
BYTE CLEAR	Automatic Before Each "Write"				

Note 1: Open Drain Output

**READ MODE**

The 28C64 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable ( $\overline{CE}$ ) is the power control and should be used for device selection. Output Enable ( $\overline{OE}$ ) is the output control and is used to gate data to the output pins independent of device selection. Assuming that addresses are stable, address access time ( $t_{ACC}$ ) is equal to the delay from  $\overline{CE}$  to output ( $t_{CE}$ ). Data is available at the outputs  $t_{OE}$  after the falling edge of  $\overline{OE}$ , assuming that  $\overline{CE}$  has been low and addresses have been stable for at least  $t_{ACC}-t_{OE}$ .

**STANDBY MODE**

The 28C64 is placed in the standby mode by applying a high signal to the  $\overline{CE}$  input. When in the standby mode, the outputs are in a high impedance state, independent of the  $\overline{OE}$  input.

**DATA PROTECTION**

In order to ensure data integrity, especially during critical power-up and power-down transitions, the following enhanced data protection circuits are incorporated:

First, an internal  $V_{CC}$  detect (3.8 volts typical) will inhibit the initiation of a non-volatile programming operation when  $V_{CC}$  is less than the  $V_{CC}$  detect circuit trip. In addition, on power-up an internal timer (5 ms typical) will inhibit the recognition of any program operation. During this period, all normal read functions will be operational. After both the  $V_{CC}$  detection and the internal timer have elapsed, normal programming operation can be performed.

Second, there is a  $\overline{WE}$  filtering circuit that prevents  $\overline{WE}$  pulses of less than 20 ns duration from initiating a write cycle.

Third, holding  $\overline{WE}$  or  $\overline{CE}$  high, or  $\overline{OE}$  low, inhibits a write cycle during power-on and power-off ( $V_{CC}$ ).

**WRITE MODE**

The 28C64 has a write cycle similar to that of a Static RAM. The write cycle is completely self-timed and initiated by a low going pulse on the  $\overline{WE}$  pin. On the falling edge of  $\overline{WE}$ , the address information is latched. On the rising edge, the data and the control pins ( $\overline{CE}$  and  $\overline{OE}$ ) are latched. The Ready/Busy pin goes to a logic low level indicating that the 28C64 is in a write cycle which signals the microprocessor host that the system bus is free for other activity. When Ready/Busy goes back to a high, the 28C64 has completed writing and is ready to accept another cycle.

**DATA POLLING**

The 28C64 features  $\overline{\text{DATA}}$  Polling to signal the completion of a byte write cycle. During a write cycle, an attempted read of the last byte written results in the data complement of I/O<sub>7</sub> (I/O<sub>0</sub> to I/O<sub>6</sub> are indeterminate). After completion of the write cycle, true data is available.  $\overline{\text{DATA}}$  polling allows a simple read/compare operation to determine the status of the chip eliminating the need for external hardware.

to or read from in the same manner as the regular memory array.

**OPTIONAL CHIP CLEAR**

All data may be cleared to 1s in a chip clear cycle by raising OE to 12 volts and bringing the WE and CE low. This procedure clears all data.

**DEVICE IDENTIFICATION**

An extra row of 32 bytes of EEPROM memory is available to the user for device identification. By raising A9 to 12V ± 0.5V and using address locations 1FEO to 1FFF, the additional bytes can be written

**RETENTION ENDURANCE**

Read retention for data written into the 28C64 is greater than 10 years, with up to 10<sup>5</sup> write cycles. There is no limit to the number of times data may be read.

**ELECTRICAL CHARACTERISTICS**

**Absolute Maximum Ratings**

Temperature under Bias .....	-10° C to +85° C (Industrial: -50° C to +95° C)
Storage Temperature .....	-65° C to +125° C
All Input Voltages with Respect to Ground .....	+6.25V to -0.6V
All Output Voltages with Respect to Ground .....	V <sub>CC</sub> +0.6V to -0.6V
Voltage on OE with Respect to Ground .....	+13.5V to -0.6V

**Note:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

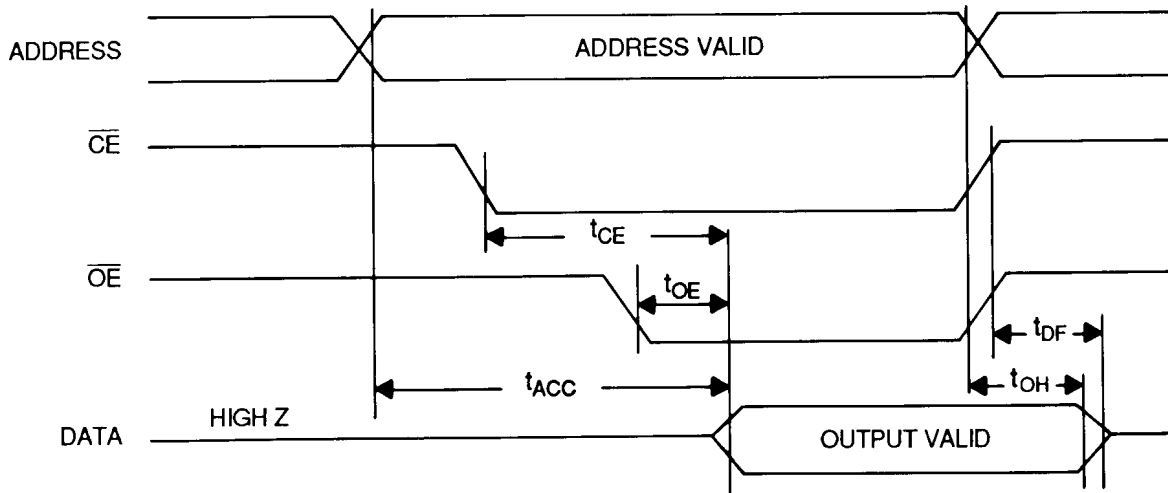
**DC CHARACTERISTICS**

28C64 T<sub>A</sub> = 0° C to +70° C, V<sub>CC</sub> = 5V ±10% unless otherwise specified.  
 28C64I T<sub>A</sub> = -40° C to +85° C, V<sub>CC</sub> = 5V ±10% unless otherwise specified.

SYMBOL	PARAMETER	MIN	MAX	UNITS	CONDITIONS
I <sub>LI</sub>	Input Leakage Current		10	μA	-0.1 to V <sub>CC</sub> +1
I <sub>LO</sub>	Output Leakage Current		10	μA	-0.1 to V <sub>CC</sub> +0.1
I <sub>CC</sub>	V <sub>CC</sub> Current Standby		100 2 3	μA mA mA	$\overline{\text{CE}} = V_{CC}-0.3$ to V <sub>CC</sub> +1 $\overline{\text{CE}} = V_{IH}$ (0° C to +70° C) $\overline{\text{CE}} = V_{IH}$ (-40° C to +85° C)
I <sub>CC</sub>	V <sub>CC</sub> Current Active		30	mA	f = 1 MHz
V <sub>IL</sub>	Input Low Voltage	-0.1	+0.8	V	
V <sub>IH</sub>	Input High Voltage	2.0	V <sub>CC</sub> +1	V	
V <sub>OL</sub>	Output Low Voltage		.45	V	I <sub>OL</sub> = 2.1 mA
V <sub>OH</sub>	Output High Voltage	2.4		V	I <sub>OH</sub> = -400 μA

**AC CHARACTERISTICS — READ CYCLE**

SYMBOL	PARAMETER	28C64-15		28C64-20		28C64-25		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX	MIN	MAX		
$t_{ACC}^{(1)}$	Address to Output Delay		150		200		250	ns	$\overline{OE} = \overline{CE} = V_{IL}$
$t_{CE}$	$\overline{CE}$ to Output Delay		150		200		250	ns	$\overline{OE} = V_{IL}$
$t_{OE}$	$\overline{OE}$ to Output Delay		70		80		120	ns	$\overline{CE} = V_{IL}$
$t_{DF}^{(2,3)}$	$\overline{OE}$ High to Output Float	0	50	0	55	0	70	ns	$\overline{CE} = V_{IL}$
$t_{OH}$	Output Hold from Address, $\overline{CE}$ or $\overline{OE}$ , whichever occurred first.		10		10		10	ns	$\overline{CE} = \overline{OE} = V_{IL}$



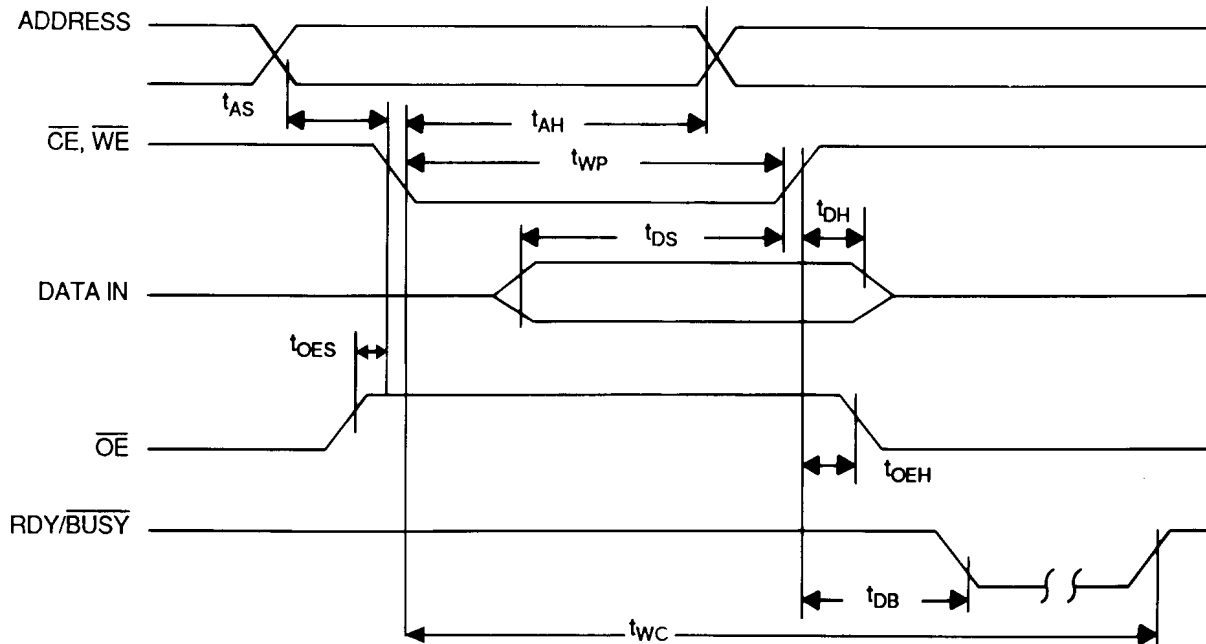
**Notes:**

- $\overline{OE}$  may be delayed up to  $t_{ACC} - t_{OE}$  after the falling edge of  $\overline{CE}$  without impact on  $t_{ACC}$ .
- This parameter is only sampled and is not 100% tested.
- $t_{DF}$  is specified from  $\overline{OE}$  to  $\overline{CE}$ , whichever occurs first.

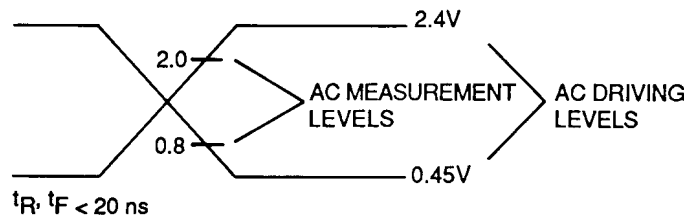
**AC CHARACTERISTICS — BYTE WRITE**

SYMBOL	PARAMETER	MIN	MAX	UNITS	COMMENTS
$t_{AS}$	Address, Setup Time	10		ns	
$t_{AH}$	Address, Hold Time	50		ns	
$t_{WP}$	Write Pulse Width	100	1000	ns	(1)
$t_{DS}$	Data Setup Time	50		ns	
$t_{DH}$	Data Hold Time	10		ns	
$t_{DB}$	Time to Device Busy		50	ns	
$t_{OEH}$	$\overline{OE}$ Hold Time	10		ns	
$t_{OES}$	$\overline{OE}$ Setup Time	10		ns	
$t_{WC}$	Write Cycle Time 28C64		1	ms	Typically 0.5 ms
	28C64F		200	$\mu s$	Typically 100 $\mu s$

Note 1: If  $t_{WP}$  is extended more than the maximum limit, data must be held valid throughout the write cycle.

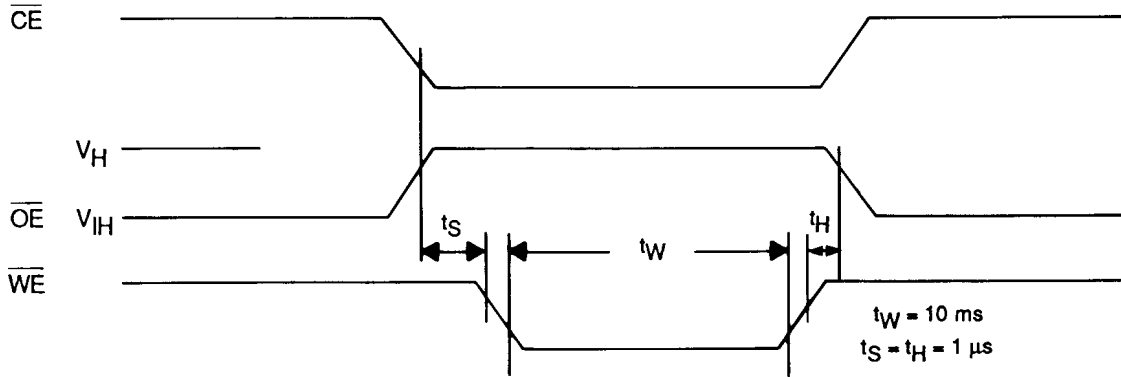


**AC TESTING, INPUT AND OUTPUT WAVEFORMS**



AC testing inputs are driven at 2.4V AC for a Logic 1 and 0.45V for a Logic 0. Timing measurements are made at 2.0V for a Logic 1 and 0.8V for a Logic 0.

**CHIP CLEAR**



**SUPPLEMENTARY CONTROL**

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$A_1$	$V_{CC}$	I/O <sub>1</sub>
Chip Clear	$V_{IL}$	$V_H$		X	$V_{CC}$	
Extra Row Read	$V_{IL}$	$V_{IL}$	$V_{IH}$	$A_9 = V_H$	$V_{CC}$	Data Out
Extra Row Write		$V_{IH}$		$A_9 = V_H$	$V_{CC}$	Data In

$V_H = 12.0 \pm 0.5$  volts.

**ORDERING INFORMATION**

**PART TYPE**

**SUFFIX**

28C64

15 - - / -  
20 I R  
25 M

J  
D  
L  
K  
W  
S

**PACKAGE**

BLANK = PLASTIC  
J = CERDIP  
D = CERAMIC  
L = PLCC  
K = CERAMIC LCC  
W = DIE IN WAFER FORM (CONSULT FACTORY)  
S = DIE IN WAFFLE PACK (CONSULT FACTORY)

**SCREENING**

BLANK = STD. COMMERCIAL/INDUSTRIAL  
R = MIL-STD-883C, METHOD 5004

**TEMP RANGE**

BLANK = 0°C TO +70°C  
I = -40° TO +85°C  
M = -55° TO +125°C (CONSULT FACTORY)

**SPEED**

15 = 150 ns  
20 = 200 ns  
25 = 250 ns

**OPTION**

BLANK =  $t_{WC} = 1$  ms,  $10^5$  CYCLES  
F =  $t_{WC} = 200 \mu s$ ,  $10^5$  CYCLES  
X =  $t_{WC} = 1$  ms, NO CONNECT PIN 1 DIP, PIN 2 LCC/PLCC

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